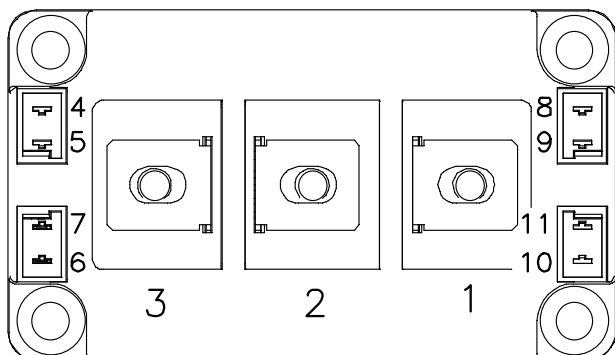
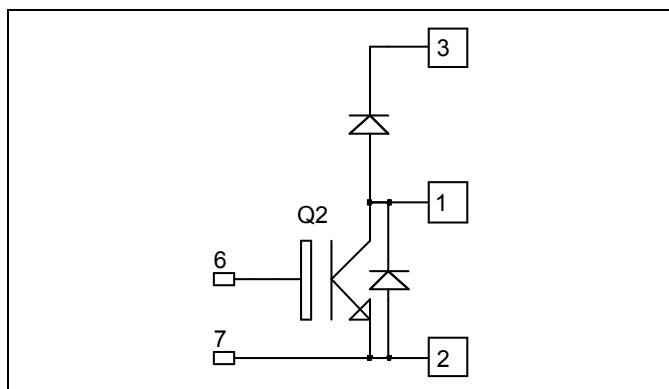


Boost chopper Trench + Field Stop IGBT4 Power Module

$V_{CES} = 1200V$
 $I_C = 700A @ T_c = 80^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	840	A
		$T_C = 80^\circ C$	700	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	1800	
V_{GE}	Gate - Emitter Voltage		± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	3000	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	1200A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
 See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			5	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 600A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.8 2.2	2.2	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 11mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			800	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		37.2		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		2.3		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		2		
Q_G	Gate charge	$V_{GE} = -8V / 15V ; V_{CE} = 600V$ $I_C = 600A$		3.4		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$ $R_G = 0.8\Omega$		200		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			380		
T_f	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$ $R_G = 0.8\Omega$		220		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			450		
T_f	Fall Time			80		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$	$T_j = 150^\circ\text{C}$	54		mJ
E_{off}	Turn-off Switching Energy	$R_G = 0.8\Omega$	$T_j = 150^\circ\text{C}$	58		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 900V$ $t_p \leq 10\mu s ; T_j = 150^\circ\text{C}$		2400		A

Chopper ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		1200			V
I_{RRM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		250 2000	μA
I_F	DC Forward Current		$T_C = 80^\circ\text{C}$	600		A
V_F	Diode Forward Voltage	$I_F = 600A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.7 1.65	2.2	V
t_{rr}	Reverse Recovery Time	$I_F = 600A$ $V_R = 600V$ $di/dt = 7000A/\mu s$	$T_j = 25^\circ\text{C}$	155		ns
			$T_j = 150^\circ\text{C}$	300		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	53 110		μC
E_{rr}	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	23 46		mJ

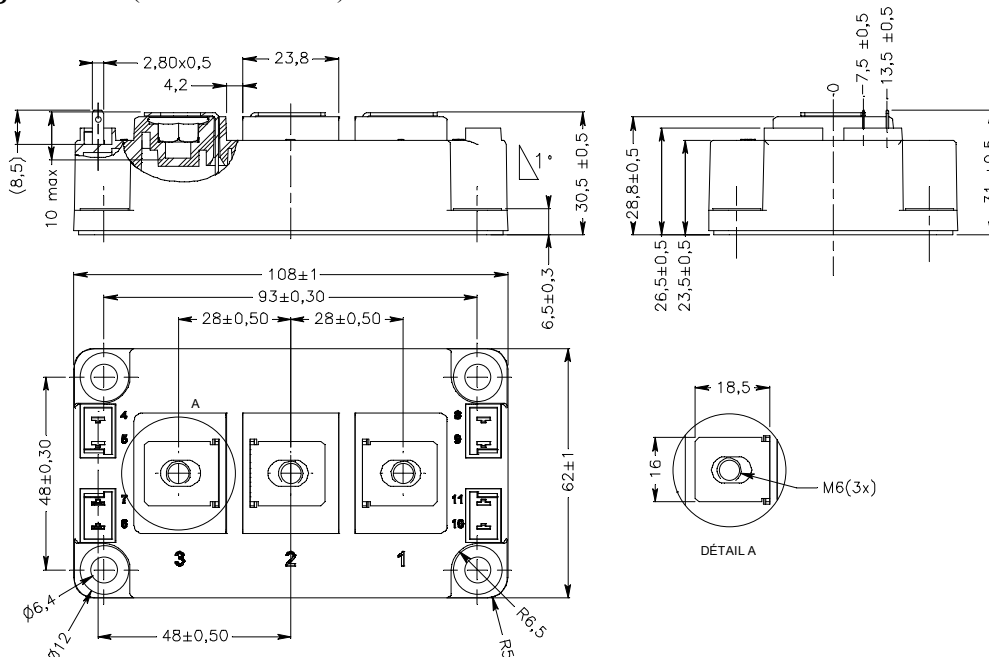
IGBT Parallel protection diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I _{RRM}	Maximum Reverse Leakage Current	V _R =1200V	T _j = 25°C			100	μA
			T _j = 150°C			500	
I _F	DC Forward Current		T _C = 80°C		75		A
V _F	Diode Forward Voltage	I _F = 75A V _{GE} = 0V	T _j = 25°C		1.7	2.2	V
			T _j = 150°C		1.65		
t _{rr}	Reverse Recovery Time	I _F = 75A V _R = 600V di/dt = 1900A/μs	T _j = 25°C		155		ns
			T _j = 150°C		300		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		7.3		μC
			T _j = 150°C		15.2		
E _{rr}	Reverse Recovery Energy		T _j = 25°C		2.6		mJ
			T _j = 150°C		5.5		

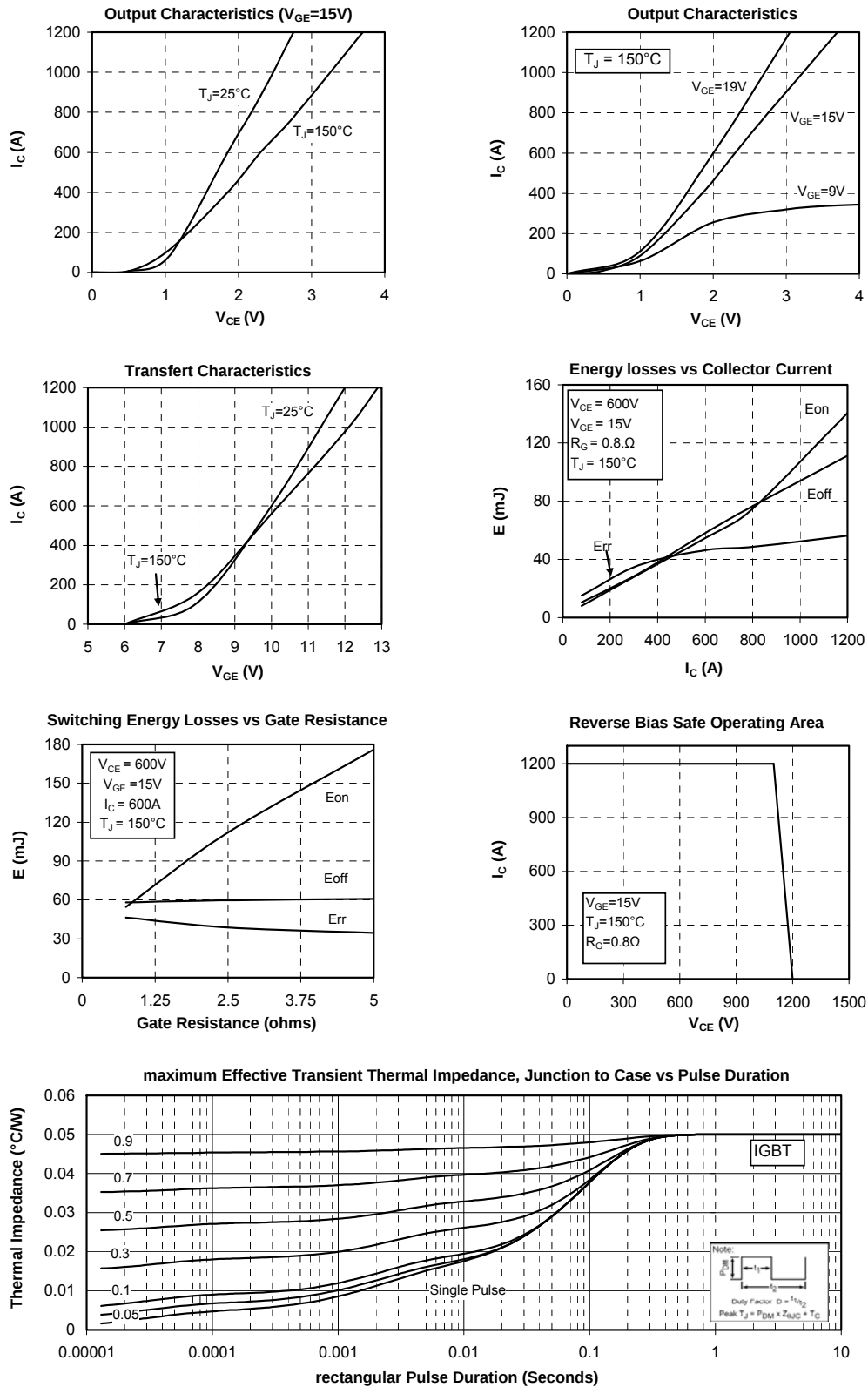
Thermal and package characteristics

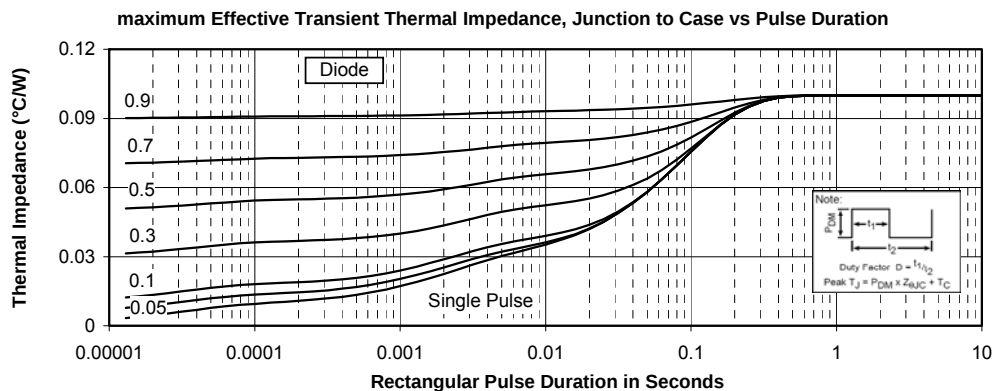
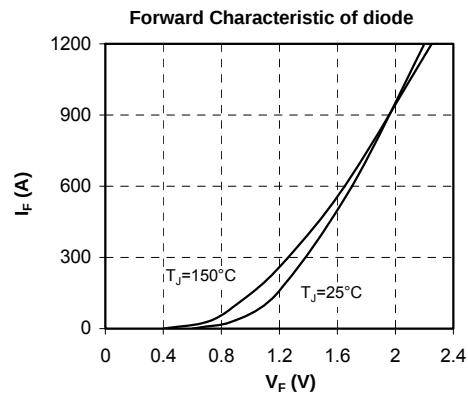
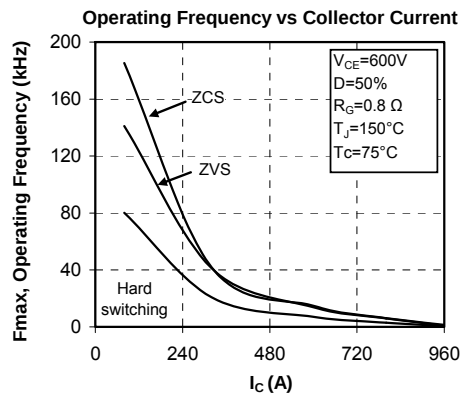
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.05	°C/W
			Chopper diode			0.10	
			IGBT parallel diode			0.62	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		175	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)



Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.

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